

1.主要用途与主要特点

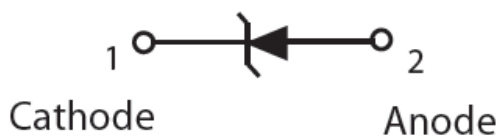
1.1 主要用途

小功率稳压管主要用于移动电话，手持设备和高密度电脑主板等产品的电路电压调整。

1.2 主要特点

- 适合高密度应用的小型化封装尺寸
- 5%的高精度稳压电压稳定性
- 高可靠性芯片和封装工艺

2. 封装管芯示意图



3. 电参数极限值

除非另有规定， $T_{amb} = 25^{\circ}\text{C}$

参 数 名 称	符号	额定值	单位
正向电压（ $I_F=10\text{mA}$ ）	V_F	0.85	V
总耗散功率	P_D	500	mW
热阻	$R_{\theta JA}$	556	$^{\circ}\text{C}/\text{W}$
热阻	$R_{\theta JA}$	417	$^{\circ}\text{C}/\text{W}$
最高工作结温	T_j	150	$^{\circ}\text{C}$
贮存温度	T_{stg}	-55~150	$^{\circ}\text{C}$

4. 电参数特性表 除非另有规定, $T_{amb} = 25^{\circ}\text{C}$

DEVICE	Marking	VZ(V) @ IZ=5mA			ZZ@ IZ1=1mA	ZZ @ IZ2 = 5 mA	ZZ @ IZ3 = 20mA	IR@VR	VR	Typical Temperature Coefficient(mV/°C)@ IZ=5mA	
		MIN	NOM	MAX	(Ω)	(Ω)	(Ω)	(uA)	V	Min	Max
BZT52 B2V4T1G	WX	2.352	2.4	2.448	600	100	50	50	1	-3.5	0
BZT52 B2V7T1G	W1	2.646	2.7	2.754	600	100	50	20	1	-3.5	0
BZT52 B3V0T1G	W2	2.94	3	3.15	600	95	50	10	1	-3.5	0
BZT52 C3V3T1G	W3	3.234	3.3	3.366	600	95	40	5	1	-3.5	0
BZT52 B3V6T1G	W4	3.528	3.6	3.672	600	90	40	5	1	-3.5	0
BZT52 B3V9T1G	W5	3.822	3.9	3.978	600	90	30	0.5	1	-3.5	0
BZT52 B4V3T1G	W6	4.214	4.3	4.386	600	90	30	0.5	1	-3.5	0
BZT52 B4V7T1G	W7	4.606	4.7	4.794	500	80	15	3.0	2	-3.5	0.2
BZT52 B5V1T1G	W8	4.998	5.1	5.202	480	60	15	2.0	2	-2.7	1.2
BZT52 B5V6T1G	W9	5.488	5.6	5.712	400	40	10	1.0	2	-2	2.5
BZT52 B6V2T1G	WA	6.076	6.2	6.324	150	9.5	5.7	2.4	4	0.4	3.7
BZT52 B6V8T1G	WB	6.664	6.8	6.936	76	14.2	5.7	1.6	4	1.2	4.5
BZT52 B7V5T1G	WC	7.35	7.5	7.65	76	14.2	5.7	0.8	5	2.5	5.3
BZT52 B8V2T1G	WD	8.036	8.2	8.364	76	14.2	5.7	0.56	5	3.2	6.2
BZT52 B9V1T1G	WE	8.918	9.1	9.282	95	14.2	7.6	0.4	7	3.8	7.0
BZT52 B10T1G	WF	9.8	10	10.2	142.5	19	9.5	0.1	8	4.5	8.0
BZT52 B11T1G	WG	10.78	11	11.22	142.5	19	9.5	0.1	8	5.4	9.0
BZT52 B12T1G	WH	11.76	12	12.24	150	23.7	9.5	0.1	8	6.0	10.0
BZT52 B13T1G	WI	12.74	13	13.26	190	28.5	14.2	0.1	8	7.0	11.0
BZT52 B15T1G	WJ	14.7	15	15.3	190	28.5	19	0.1	11	9.2	13.0
BZT52 B16T1G	WK	15.68	16	16.32	190	38	19	0.1	11	10.4	14.0
BZT52 B18T1G	WL	17.64	18	18.36	213	42.7	19	0.1	13	12.4	16.0
BZT52 B20T1G	WM	19.6	20	20.4	213	52.2	19	0.1	14	14.4	18.0
BZT52 B22T1G	WN	21.56	22	22.44	237	52.2	23.7	0.1	15	16.4	20.0
BZT52 B24T1G	WO	23.52	24	24.48	250	66.5	23.7	0.1	17	18.4	22.0

4. 电参数特性表 除非另有规定, $T_{amb} = 25^{\circ}\text{C}$

DEVICE	Marking	VZ(V) @ IZ=2mA			ZZ @ IZ = 0.5 mA	ZZ @ IZ = 2 mA	ZZ @ IZ = 10mA	IR@VR	VR	Typical Temperature Coefficient(mV/°C)@ IZ=2mA	
		MIN	NOM	MAX	(Ω)	(Ω)	(Ω)	(uA)	V	Min	Max
BZT52B27T1G	WP	26.46	27	27.54	295	75	43	0.04	19	21.4	25.3
BZT52B30T1G	WQ	29.4	30	30.6	295	75	48	0.04	21	24.4	29.4
BZT52B33T1G	WR	32.34	33	33.66	320	75	53	0.04	23	27.4	33.4
BZT52B36T1G	WS	35.28	36	36.72	345	85	58	0.04	25	30.4	37.4
BZT52B39T1G	WT	38.22	39	39.78	345	125	68	0.04	27	33.4	41.2
BZT52B43T1G	WU	42.14	43	43.86	370	145	78	0.04	30	37.6	46.6
BZT52B47T1G	WV	46.06	47	47.94	370	165	88	0.04	33	42.0	51.8
BZT52B51T1G	WW	49.98	51	52.02	395	175	98	0.04	36	46.6	57.2
BZT52B56T1G	XW	54.88	56	57.12	420	195	108	0.04	39	52.2	63.8
BZT52B62T1G	6E	60.76	62	63.24	445	210	118	0.04	43	58.8	71.6
BZT52B68T1G	6F	66.64	68	69.36	470	235	128	0.04	48	65.6	79.8
BZT52B75T1G	6H	73.5	75	76.5	495	250	138	0.04	53	73.4	88.6

5. 特性曲线图表

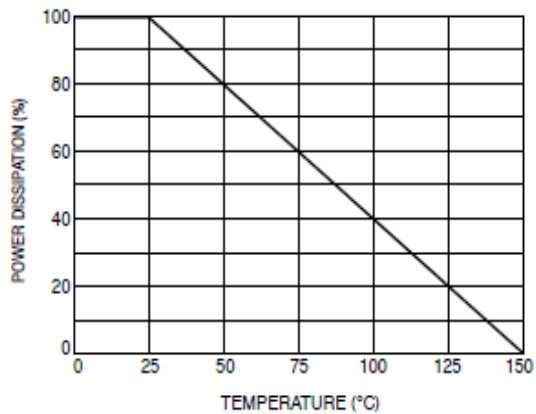


图 1 最大连续功率损耗

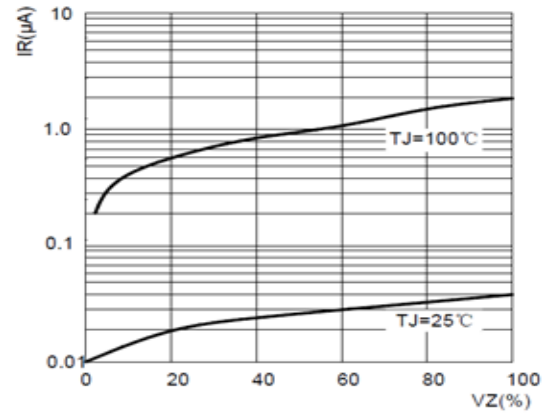


图 2 典型反向特性

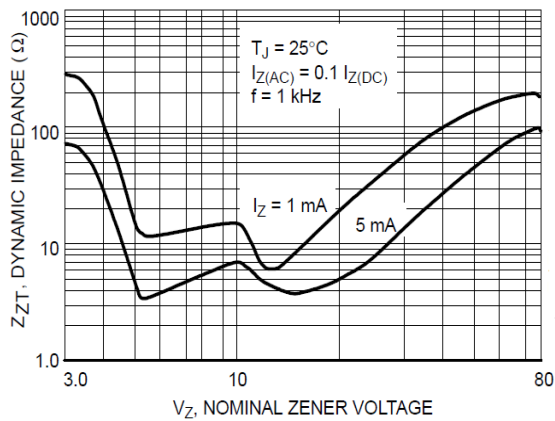


图 3 反向电压与阻抗特性曲线

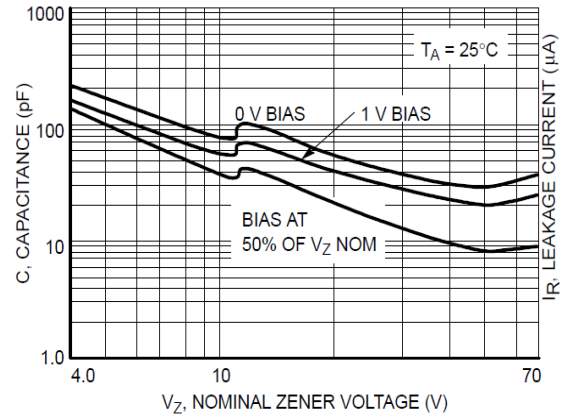
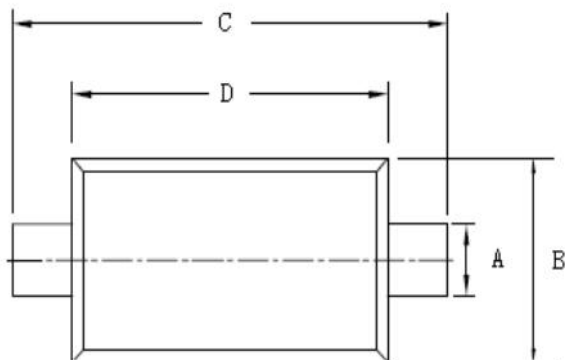
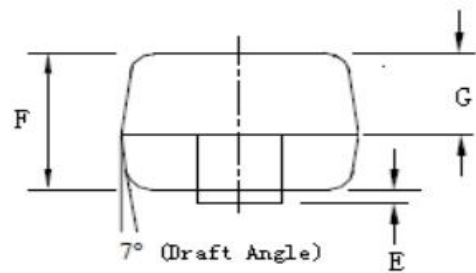
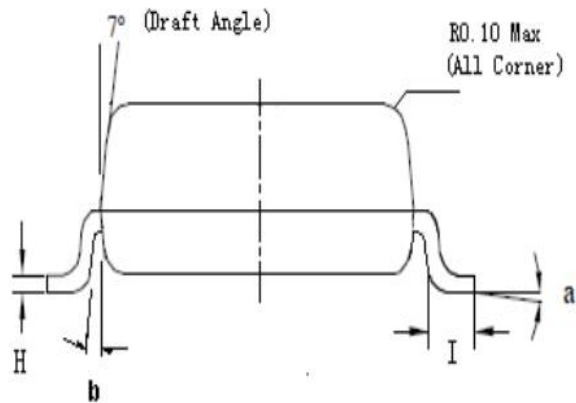


图 4 典型电容特性曲线

SOD123 Package Mechanical Data



Symbol	Dim in mm		
	Min	Nom	Max
A	0.520	0.550	0.570
B	1.400	1.550	1.700
C	3.550	3.650	3.850
D	2.550	2.650	2.850
E	0.000	0.050	0.100
F	1.050	1.100	1.150
G	0.620	0.650	0.670
H	0.090	0.100	0.110
I	0.250	0.350	0.450
a	0°	—	6°
b	0.4°	—	0.8°